Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

H928S

AUDIO POWER AMPLFIER APPLICATIONS

ABSOLUTE MAXIMUM RATINGS (T_a=25℃)

T_{stg}——Storage Temperature····· -55~150℃

T_j——Junction Temperature·····150℃

P_C——Collector Dissipation·····-750mW

V_{CBO}——Collector-Base Voltage·····-30V

V_{CEO}——Collector-Emitter Voltage·····-30V

V_{EBO}——Emitter-Base Voltage·····-5V

I_C——Collector Current·····-2A

TO-92

1—Emitter，E
2—Collector，C
3—Base，B

ELECTRICAL CHARACTERISTICS (T_a=25℃)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-30			V	I_C=-100μA, I_E=0
BV_{CEO}	Collector-Emitter Breakdown Voltage	-30			V	I_C=-10mA, I_B=0
BV_{EBO}	Emitter-Base Breakdown Voltage	5			V	I_E=-1mA，I_C=0
I_{CBO}	Collector Cut-off Current			-100	nA	V_{CB}=-30V, I_E=0
I_{EBO}	Emitter-Base Cut-off Current			-100	nA	V_{EB}=-5V, I_C=0
H_{FE}	DC Current Gain	100		320		V_{CE}=-2V, I_C=-500mA
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			-2	V	I_C=-1.5mA, I_B=-30mA
$V_{BE(ON)}$	Base-Emitter On Voltage			-1	V	V_{CE}=-2V, I_C=-500mA
f_T	Current Gain-Bandwidth Product		120		MHz	V_{CE}=-2V, I_C=-500mA
Cob	Collector-Base Capacitance		48		pF	V_{CB}=-10V, I_E=0，F=1MHz

h_{FE} Classification

O	Y
100—200	160—320